

CMKD6263

ULTRAmi™
TRIPLE ISOLATED
HIGH VOLTAGE
SCHOTTKY DIODE

ULTRAmi™



SOT-363 CASE

Central™
Semiconductor Corp.

FEATURES:

- MEETS GALVANIC ISOLATION REQUIREMENTS OF IEEE 1394
- HIGH VOLTAGE (70V)
- ULTRAmi™ PACKAGE
- REQUIRES LESS BOARD SPACE THAN 3 INDIVIDUAL DIODES
- LOW FORWARD VOLTAGE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6263 contains three Galvanically isolated, High Voltage Silicon Schottky diodes, epoxy molded in an ULTRAmi™ surface mount package, designed for fast switching applications requiring a low forward voltage drop. MARKING CODE: K63.

MAXIMUM RATINGS: PER DIODE ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	70	V
Continuous Forward Current	I_F	15	mA
Forward Surge Current, $t_p=1.0$ s	I_{FSM}	50	mA
Power Dissipation	P_D	250	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: PER DIODE ($T_A=25^\circ\text{C}$)

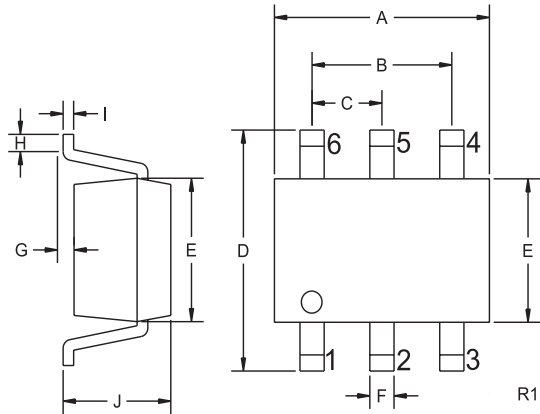
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_R	$I_R=10\mu\text{A}$	70			V
V_F	$I_F=1.0\text{mA}$		395	410	mV
I_R	$V_R=50\text{V}$		98	200	nA
C_T	$V_R=0\text{V}$, $f=1.0\text{MHz}$			2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}$, $I_{rr}=1\text{mA}$, $R_L=100\Omega$			5.0	ns

R0 (30-August 2001)

SOT-363 CASE - MECHANICAL OUTLINE

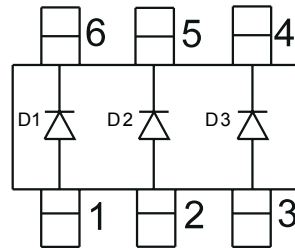
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)



LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1



MARKING CODE: K63